NT	Utech
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## CS/B.TECH(ECE)/SEM-6 /EC-604/2012 2012

### **VLSI CIRCUITS AND SYSTEMS**

Time Allotted: 3 Hours Full Marks: 70

The figures in the margin indicate full marks.

Candidates are required to give their answers in their own words as far as practicable.

#### **GROUP - A**

#### ( Multiple Choice Type Questions )

- 1. Choose the correct alternatives for any  $\emph{ten}$  of the following :  $10 \times 1 = 10$ 
  - i) The noise margin for high signal levels  $\left(NM_{H}\right)$  is
    - a)  $V_{IL} V_{OL}$
- b)  $V_{OH} V_{IH}$
- c)  $V_{OH} V_{OH}$
- d) none of these.
- ii) The switching threshold voltage of CMOS inverter is obtained when
  - a)  $V_{in} = V_{out}$
- b)  $V_{T,n} = -V_{T,p}$
- c)  $V_{in} = 2V_{out}$
- d) none of these.
- iii) In CMOS static logic design, total number of transistors required for the Boolean function F = A + (B + CD) is
  - a) 10

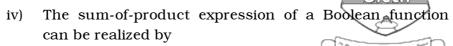
b) 8

c) 5

d) none of these.

6404

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- a) AOI gates
- b) OAI gates
- c) both (a) and (b)
- d) none of these.
- v) Dynamic logic circuit is
  - a) faster than static design
  - b) slower than static design
  - c) bigger than static design
  - d) none of these.
- vi) VHDL is used for
  - a) Timing analysis
- b) layout diagram
- c) logic design
- d) RTL coding.
- vii) Active resistor is used for
  - a) less fabrication area
  - b) load resistor
  - c) constant current source
  - d) all of these.
- viii) For depletion type NMOS
  - a) the threshold voltage is + ve
  - b) the threshold voltage is -ve
  - c) the threshold voltage is ve and + ve
  - d) all of these.
- ix) BiCMOS means
  - a) two BJT circuits
  - b) two CMOS circuits
  - c) both BJT and CMOS circuits
  - d) none of these.
- x) For a symmetrical CMOS inverter the relation between aspect ratio of NMOS and PMOS is
  - a) (W/L)p = (W/L)n
- b) (W/L)p = 2.5 (W/L)n
- c) (W/L)n = 2.5 (W/L)p d)
- (W/L)p = 5 (W/L)n.



- xi) Pseudo *n*MOS logic provides which of the following advantages?
  - a) Static power dissipation is less compared to CMOS logic
  - b) It is faster compared to other logics
  - c) It requires less no. of transistors compared to CMOS logic
  - d) It is more noise immune.
- xii) Configurable logic blocks are used in
  - a) gate array design style
  - b) standard cell based design
  - c) field programmable gate array layout
  - d) full custom design.

#### **GROUP - B**

#### (Short Answer Type Questions)

Answer any *three* of the following.

 $3 \times 5 = 15$ 

- 2. What is current source and current sink in VLSI circuit? Design a current sink using  $V_{DD} = -V_{SS} = 2 \cdot 5 \text{V}$  to sink a current of  $10\mu\text{A}$ . Estimate the minimum voltage across the current source and the output resistance. Assume  $K_P = 50\mu\text{A}/\text{V}^2$ ,  $L = 5\mu\text{m}$ ,  $V_{THN} = 0 \cdot 83 \text{V}$ ,  $\lambda = 0 \cdot 06$ . 2 + 3
- 3. Draw and explain the operation of MOS Switched Capacitor Integrator and also find the expression for output voltage.
- 4. Compare between static logic and dynamic logic. Explain the operation of Domino-logic to design any CMOS circuit. 2+3
- 5. What is Transmission Gate (TG) ? Explain the operation of Edge Triggered D Flip-Flop using CMOS TG gates. Implement the expression using CMOS TG logic. Z = XY' + X'Y. (X' = complement of X)
- 6. Draw the circuit of a CMOS full adder circuit and explain its operation.

#### **GROUP - C**

# ( Long Answer Type Questions)

Answer any three of the following.

 $3 \times 15 = 45$ 

- 7. a) Explain the fabrication process steps for an NMOS transistor with necessary diagrams.
  - b) Write down the difference between twin-tub process and P-well process.
  - c) Draw the layout of the following:

i) F = AB + CD (ii) F = A + BC

7 + 3 + 5

- 8. a) Explain how CMOS can be used for inverter logic. Draw the voltage transfer characteristics of CMOS inverter and clearly define operating regions of NMOS and PMOS.
  - b) Show that for a symmetric CMOS inverter the two noise margins are same and are equal to VIL. Also show that for ideal CMOS inverter  $(W/L)p = 2 \cdot 5 (W/L)n$ .

3 + 3 + 3 + 3 + 3

- 9. a) What is CMRR?
  - b) Explain with a circuit diagram, operation of a differential amplifier.
  - c) Explain briefly different stages of an OP-AMP with the help of a block diagram. 2 + 7 + 6
- 10. a) What do you mean by current sink and current source?
  - b) Explain how combination of switches and capacitors can be used to emulate a resistor.
  - c) What is phase locked loop? Explain its operation. Mention two uses of phase locked loop.

2 + 5 + 2 + 5 + 1

- 11. Write short notes on any *three* of the following :
- $3 \times 5$

- a) Constant voltage scaling
- b) CMOS NORA logic
- c) ASIC
- d) DCVSL and pseudo n-MOS inverter.

6404 4